Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-19.(Canceled)

20.(Currently Amended) A semiconductor device having a thin film transistor, the thin film transistor comprising:

a semiconductor layer on an insulating surface, wherein the semiconductor layer has a side ~~recessed portion~~ recess ~~formed by overetching~~;

a gate electrode adjacent to the semiconductor layer with a gate insulating film interposed therebetween; and

[an] a source electrode in contact with the semiconductor layer, wherein the source electrode contains a first layer and a second layer, and

wherein the side ~~recessed portion~~ recess is filled with the first layer.

21-27.(Canceled)

28.(Previously Presented) The semiconductor device having a thin film transistor according to claim 20, wherein the semiconductor layer contains crystalline silicon.

29.(Previously Presented) The semiconductor device having a thin film transistor according to claim 20, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

30.(Previously Presented) The semiconductor device having a thin film transistor according to claim 20, wherein the first layer is an alloy of aluminum and germanium.

31.(Previously Presented) The semiconductor device having a thin film transistor according to claim 20, wherein the second layer contains aluminum.

32. (Canceled)

33.(Previously Presented) The semiconductor device having a thin film transistor according to claim 20, wherein the semiconductor device is an active matrix type EL display device.

34.(Currently Amended) A semiconductor device having a thin film transistor, the thin film transistor comprising:

a semiconductor layer on an insulating surface, wherein the semiconductor layer has a first side ~~recessed portion~~ recess ~~formed by overetching~~;

a gate electrode adjacent to the semiconductor layer with a gate insulating film interposed therebetween, wherein the gate electrode has a second side ~~recessed portion~~ recess ~~formed by overetching~~; and

[an] a source electrode in contact with the semiconductor layer and a wiring in contact with the gate electrode,

wherein ~~each of~~ the source electrode ~~and the wiring~~ contains a first layer and a second layer, [and]

wherein the wiring contains a third layer and the fourth layer,

wherein the first side ~~recessed portion~~ recess ~~and the second side recessed portion are~~ is filled with the first layer, and

wherein the second side recess is filled with the third layer.

35.(Previously Presented) The semiconductor device having a thin film transistor according to claim 34, wherein the semiconductor layer contains crystalline silicon.

36.(Previously Presented) The semiconductor device having a thin film transistor according to claim 34, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

37.(Previously Presented) The semiconductor device having a thin film transistor according to claim 34, wherein the first layer is an alloy of aluminum and germanium.

38.(Previously Presented) The semiconductor device having a thin film transistor according to claim 34, wherein the second layer contains aluminum.

39. Canceled.

40.(Previously Presented) The semiconductor device having a thin film transistor according to claim 34, wherein the semiconductor device is an active matrix type EL display device.

41.(Currently Amended) A semiconductor device having a thin film transistor, the thin film transistor comprising:

a semiconductor layer on an insulating surface, wherein the semiconductor layer has a side ~~recessed portion~~ recess ~~formed by overetching~~;

a gate insulating film on the semiconductor layer;

a gate electrode on the gate insulating film;

an interlayer insulating film over at least the gate electrode; and

[an] a source electrode over the interlayer insulating film, wherein the source electrode is in contact with the semiconductor layer through a contact hole opened in the interlayer insulating film, wherein the source electrode contains a first layer and a second layer, and

wherein the side ~~recessed portion~~ recess is filled with the first layer.

42.(Previously Presented) The semiconductor device having a thin film transistor according to claim 41, wherein the semiconductor layer contains crystalline silicon.

43.(Previously Presented) The semiconductor device having a thin film transistor according to claim 41, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

44.(Previously Presented) The semiconductor device having a thin film transistor according to claim 41, wherein the first layer is an alloy of aluminum and germanium.

45.(Previously Presented) The semiconductor device having a thin film transistor according to claim 41, wherein the second layer contains aluminum.

46. Canceled.

47.(Previously Presented) The semiconductor device having a thin film transistor according to claim 41, wherein the interlayer insulating film contains at least one selected from the group consisting of silicon oxide, silicon nitride and silicon oxynitride.

48.(Previously Presented) The semiconductor device having a thin film transistor according to claim 41, wherein the semiconductor device is an active matrix type EL display device.

49.(Currently Amended) A semiconductor device having a thin film transistor, the thin film transistor comprising:

a semiconductor layer on an insulating surface, wherein the semiconductor layer has a first side ~~recessed portion~~ recess ~~formed by overetching~~;

a gate insulating film on the semiconductor layer;

a gate electrode on the gate insulating film, wherein the gate electrode has a second side ~~recessed portion~~ recess ~~formed by overetching~~;

an interlayer insulating film over at least the gate electrode; and

[an] a source electrode and a wiring over the interlayer insulating film, wherein the source electrode is in contact with the semiconductor layer and the wiring is in contact with the gate electrode each through a contact hole opened in the interlayer insulating film, wherein ~~each of~~ the source electrode ~~and the wiring~~ contains a first layer and a second layer and the wiring contains a third layer and a fourth layer, and

wherein the first side ~~recessed portion~~ recess ~~and the second side recessed portion are~~ is filled with the first layer, and

wherein the second side recess is filled with the third layer.

50.(Previously Presented) The semiconductor device having a thin film transistor according to claim 49, wherein the semiconductor layer contains crystalline silicon.

51.(Previously Presented) The semiconductor device having a thin film transistor according to claim 49, wherein the first layer contains at least one selected from the group consisting of germanium, tin, gallium, zinc, lead, indium, and antimony.

52.(Previously Presented) The semiconductor device having a thin film transistor according to claim 49, wherein the first layer is an alloy of aluminum and germanium.

53.(Previously Presented) The semiconductor device having a thin film transistor according to claim 49, wherein the second layer contains aluminum.

54. Canceled.

55.(Previously Presented) The semiconductor device having a thin film transistor according to claim 49, wherein the interlayer insulating film contains at least one selected from the group consisting of silicon oxide, silicon nitride and silicon oxynitride.

56.(Previously Presented) The semiconductor device having a thin film transistor according to claim 49, wherein the semiconductor device is an active matrix type EL display device.